Title (en)

AlGaInN single-crystal wafer

Title (de)

Einkristall-Scheibe aus AlGaInN

Title (fr)

Plaquette monocristalline de AlGaInN

Publication

EP 1602752 A1 20051207 (EN)

Application

EP 05011927 A 20050602

Priority

JP 2004167377 A 20040604

Abstract (en)

AlGaInN single-crystal wafer with alleviated cracking and improved utilization rate and cost effectiveness. A hexagonal AlxGayIn1-(x+y)N (0 < x ≤ 1, 0 ≤ y < 1, x + y ≤ 1) single-crystal wafer, characterized in that the wafer has a thickness T (cm) and a principal face with a surface area S (cm<2>), the area S and thickness T satisfying the conditions S ≥ 10 cm<2> and 0.006S ≥ T ≥ 0.002S. <IMAGE>

IPC 1-7

C30B 29/40; C30B 23/00

IPC 8 full level

H01L 21/02 (2006.01); **C30B 23/00** (2006.01); **C30B 29/40** (2006.01)

CPC (source: EP KR US)

C30B 23/00 (2013.01 - EP US); **C30B 29/403** (2013.01 - EP US); **H01L 21/02** (2013.01 - KR)

Citation (search report)

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DE FR GB NL

DOCDB simple family (publication)

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DOCDB simple family (application)

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